

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|---|------------------|---------|------------------|
| L1 | 41708 | (gallium adj nitride) or GaN | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/07/25 12:02 |
| L2 | 11841 | L1 and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/07/25 12:02 |
| L3 | 259 | L2 and (atomic adj nitrogen or nitriding) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/07/25 12:02 |
| L4 | 991 | (438/194,285,574,767,775,777). CCLS. | US-PGPUB; USPAT | OR | OFF | 2006/07/25 13:43 |
| L5 | 0 | (gallium nitride or GaN) and (aluminum layer) and (atomic nitrogen) and (catalytic member) and gate and source and drain | US-PGPUB; USPAT | ADJ | ON | 2006/07/25 13:47 |